IN THE SPECIFICATION:

Please replace paragraph [0001] with the following rewritten paragraph:

[0001] This application claims priority to U.S. Provisional Application No. 60/268,337, filed February 12, 2001; U.S. Provisional Application No. 60/279,256, filed March 27, 2001; U.S. Provisional Application No. 60/311,609, filed August 9, 2001; U.S. Provisional Application No. 60/323,649, filed September 19, 2001; U.S. Provisional Application No. 60/332,696, filed November 13, 2001; U.S. Provisional Application No. 60/333,724, filed November 28, 2001; and U.S. Provisional Application No. 60/340,454, filed December 7, 2001; all of which are hereby incorporated by reference in their entireties. This application is related to, and incorporates by reference in their entireties, co-owned and co-pending U.S. Patent Application Serial Numbers: 10/074,563; 10/074,149; 10/074,722; 10/074,633; and 10/074,564, all of which were filed on February 11, 2002.

Please delete paragraph [0002].

Please replace paragraph [0107] with the following rewritten paragraph:

[0107] A series of Si-containing films were deposited onto a SiO_2 substrate (without a nucleation layer) at a pressure of 40 torr using trisilane and germane. The trisilane flow rate was constant at 77 sccm (hydrogen carrier, bubbler) for the examples of Table 10. Germane flow (10% germane, 90% H_2) and deposition temperature were varied as shown in Table 10. Germanium concentration (atomic %) and thickness of the resulting SiGe films were determined by RBS, and surface roughness was determined by atomic force microscopy (AFM). The results shown in Table 10 demonstrate that highly uniform films can be prepared over a range of temperatures and flow rate conditions, particularly over a large range of germane concentration. High deposition rates are achieved at relatively low temperatures without sacrificing uniformity.

Please replace the table heading that appears after paragraph [0107] with the following rewritten heading: